

Automotive N- and P-Channel 100 V (D-S) 175 °C MOSFET

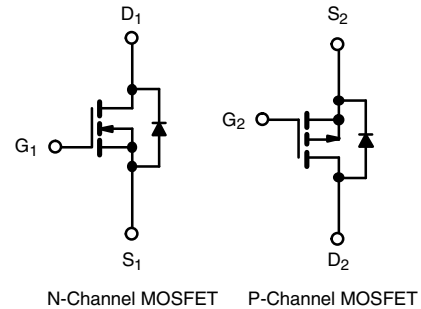
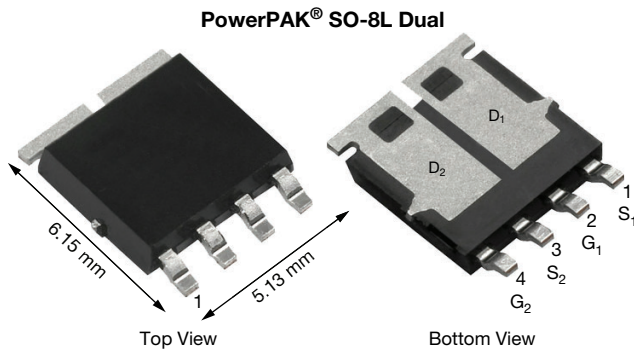
 AUTOMOTIVE
GRADE

RoHS
COMPLIANT
HALOGEN
FREE

PRODUCT SUMMARY		
	N-CHANNEL	P-CHANNEL
V_{DS} (V)	100	-100
$R_{DS(on)}$ (Ω) at $V_{GS} = \pm 10$ V	0.0450	0.1460
$R_{DS(on)}$ (Ω) at $V_{GS} = \pm 4.5$ V	0.0580	0.2065
I_D (A)	15	-9.5
Configuration	N- and P-Pair	
Package	PowerPAK SO-8L Dual	

FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R_G and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Drain-Source Voltage	V_{DS}	100	-100	V
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	I_D	$T_C = 25$ °C	15 ^a	A
		$T_C = 125$ °C	9.6	
Continuous Source Current (Diode conduction) ^a	I_S	15	-15	A
Pulsed Drain Current ^b	I_{DM}	40	-21	
Single Pulse Avalanche Current	I_{AS}	13	-6	
Single Pulse Avalanche Energy	E_{AS}	L = 0.1 mH	8.4	mJ
Maximum Power Dissipation ^b			$T_C = 25$ °C	
		$T_C = 125$ °C	9	9
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175		°C
Soldering Recommendations (Peak temperature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	N-CHANNEL	P-CHANNEL	UNIT
Junction-to-Ambient	R_{thJA}	85	85	°C/W
Junction-to-Case (Drain)				

Notes

- Package limited.
- Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
- When mounted on 1" square PCB (FR4 material).
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.



SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	100	-	-	V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-100	-	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	1.5	2	2.5	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-1.5	-2	-2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch	-	-	± 100	nA
			P-Ch	-	-	± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = 100\text{ V}$	N-Ch	-	-	1
		$V_{GS} = 0\text{ V}$	$V_{DS} = -100\text{ V}$	P-Ch	-	-	-1
		$V_{GS} = 0\text{ V}$	$V_{DS} = 100\text{ V}, T_J = 125\text{ }^\circ\text{C}$	N-Ch	-	-	50
		$V_{GS} = 0\text{ V}$	$V_{DS} = -100\text{ V}, T_J = 125\text{ }^\circ\text{C}$	P-Ch	-	-	-50
		$V_{GS} = 0\text{ V}$	$V_{DS} = 100\text{ V}, T_J = 175\text{ }^\circ\text{C}$	N-Ch	-	-	150
		$V_{GS} = 0\text{ V}$	$V_{DS} = -100\text{ V}, T_J = 175\text{ }^\circ\text{C}$	P-Ch	-	-	-150
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}$	$V_{DS} \geq 5\text{ V}$	N-Ch	10	-	A
		$V_{GS} = -10\text{ V}$	$V_{DS} \leq 5\text{ V}$	P-Ch	-6	-	-
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}$	N-Ch	-	0.0365	0.0450
		$V_{GS} = -10\text{ V}$	$I_D = -6\text{ A}$	P-Ch	-	0.1184	0.1460
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 125\text{ }^\circ\text{C}$	N-Ch	-	-	0.0774
		$V_{GS} = -10\text{ V}$	$I_D = -6\text{ A}, T_J = 125\text{ }^\circ\text{C}$	P-Ch	-	-	0.2435
		$V_{GS} = 10\text{ V}$	$I_D = 6\text{ A}, T_J = 175\text{ }^\circ\text{C}$	N-Ch	-	-	0.0978
		$V_{GS} = -10\text{ V}$	$I_D = -6\text{ A}, T_J = 175\text{ }^\circ\text{C}$	P-Ch	-	-	0.2994
		$V_{GS} = 4.5\text{ V}$	$I_D = 4\text{ A}$	N-Ch	-	0.0468	0.0580
		$V_{GS} = -4.5\text{ V}$	$I_D = -4\text{ A}$	P-Ch	-	0.1669	0.2065
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 6\text{ A}$	N-Ch	-	15	-	S
		$V_{DS} = -15\text{ V}, I_D = -6\text{ A}$	P-Ch	-	7	-	
Dynamic ^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch	-	420	600
		$V_{GS} = 0\text{ V}$	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P-Ch	-	480	650
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch	-	260	350
		$V_{GS} = 0\text{ V}$	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P-Ch	-	250	350
Reverse Transfer Capacitance	C_{rss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	N-Ch	-	17	25
		$V_{GS} = 0\text{ V}$	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	P-Ch	-	20	30
Total Gate Charge ^c	Q_g	$V_{GS} = 10\text{ V}$	$V_{DS} = 50\text{ V}, I_D = 1\text{ A}$	N-Ch	-	9	15
		$V_{GS} = -10\text{ V}$	$V_{DS} = -50\text{ V}, I_D = -1\text{ A}$	P-Ch	-	12	20
Gate-Source Charge ^c	Q_{gs}	$V_{GS} = 10\text{ V}$	$V_{DS} = 50\text{ V}, I_D = 1\text{ A}$	N-Ch	-	1.2	-
		$V_{GS} = -10\text{ V}$	$V_{DS} = -50\text{ V}, I_D = -1\text{ A}$	P-Ch	-	2	-
Gate-Drain Charge ^c	Q_{gd}	$V_{GS} = 10\text{ V}$	$V_{DS} = 50\text{ V}, I_D = 1\text{ A}$	N-Ch	-	1.9	-
		$V_{GS} = -10\text{ V}$	$V_{DS} = -50\text{ V}, I_D = -1\text{ A}$	P-Ch	-	3	-
Gate Resistance	R_g	$f = 1\text{ MHz}$		N-Ch	1.3	2.7	4.5
				P-Ch	5	10.2	15.5
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$		N-Ch	-	8	15
		$V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$		P-Ch	-	12	20
Rise Time ^c	t_r	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$		N-Ch	-	4	10
		$V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$		P-Ch	-	5	10
Turn-Off Delay Time ^c	$t_{d(off)}$	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$		N-Ch	-	20	35
		$V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$		P-Ch	-	30	50
Fall Time ^c	t_f	$V_{DD} = 50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_g = 5\text{ }\Omega$		N-Ch	-	17	30
		$V_{DD} = -50\text{ V}, R_L = 50\text{ }\Omega, I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 5\text{ }\Omega$		P-Ch	-	15	25



SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}		N-Ch	-	-	40	A
			P-Ch	-	-	-21	
Forward Voltage	V _{SD}	I _S = 6 A	N-Ch	-	0.89	1.2	V
		I _S = -6 A	P-Ch	-	-0.89	-1.2	

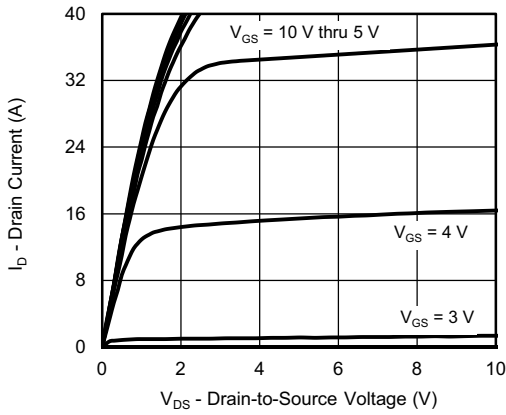
Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

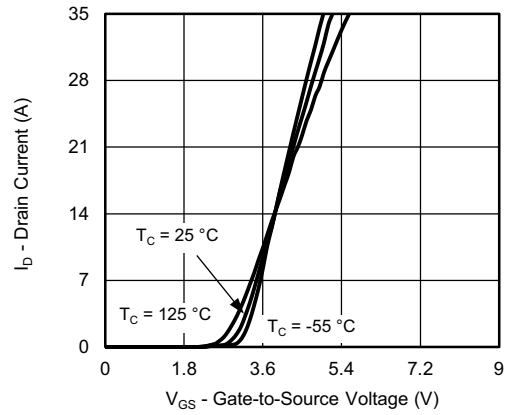
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



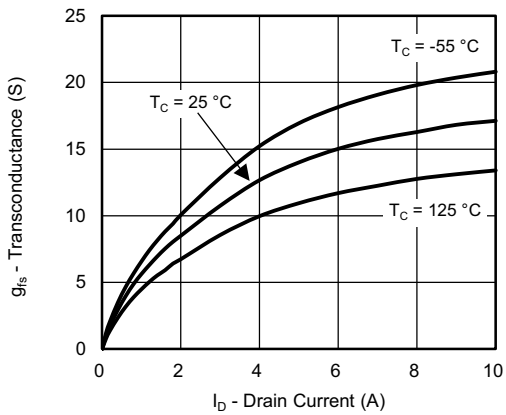
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



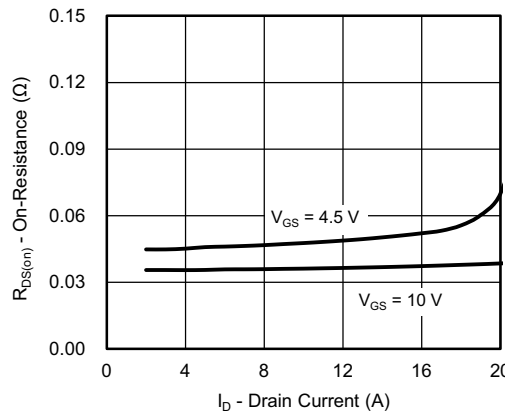
Output Characteristics



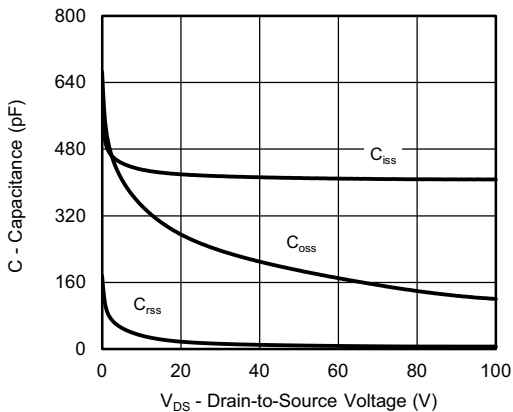
Transfer Characteristics



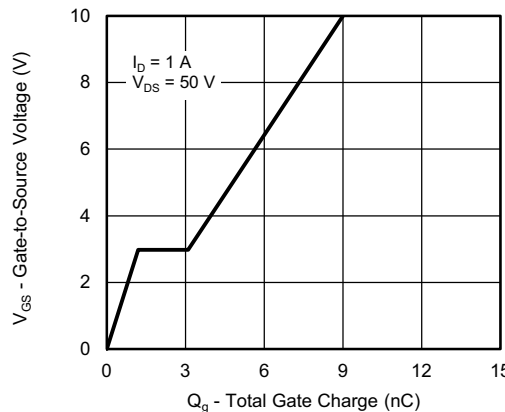
Transconductance



On-Resistance vs. Drain Current



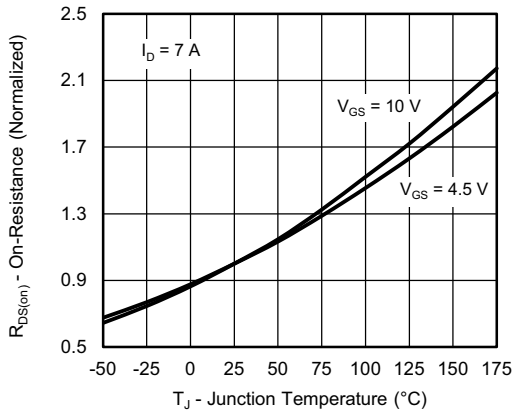
Capacitance



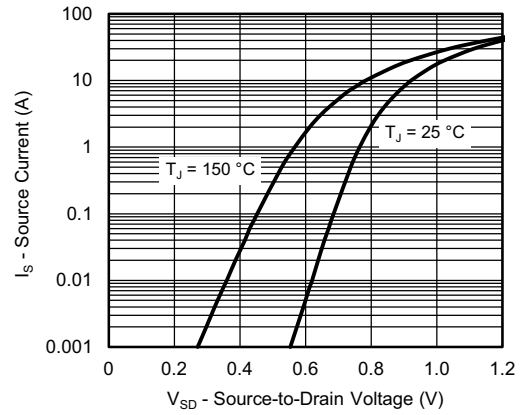
Gate Charge



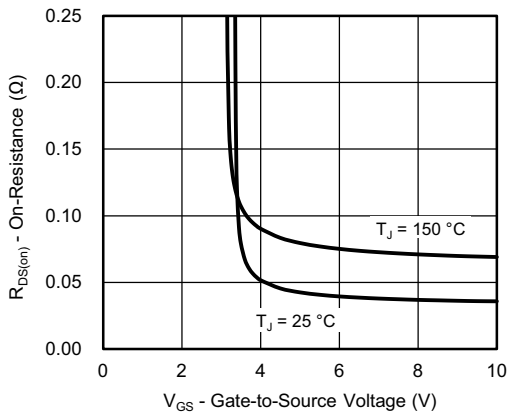
N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



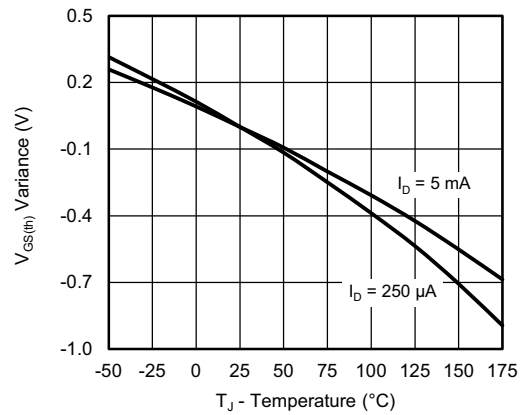
On-Resistance vs. Junction Temperature



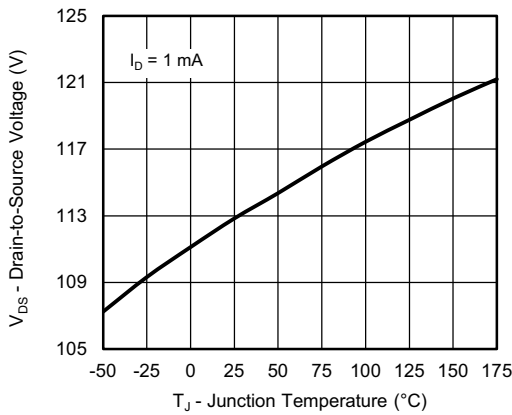
Source Drain Diode Forward Voltage



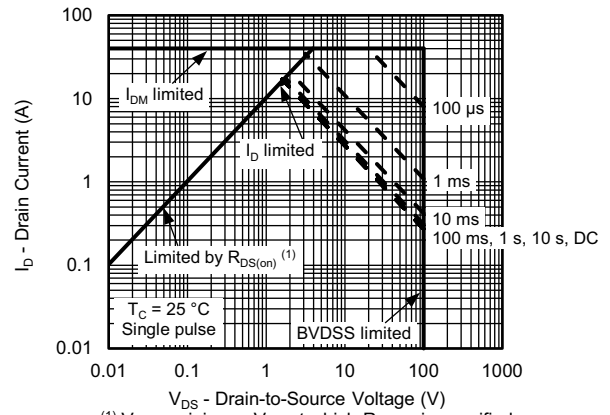
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

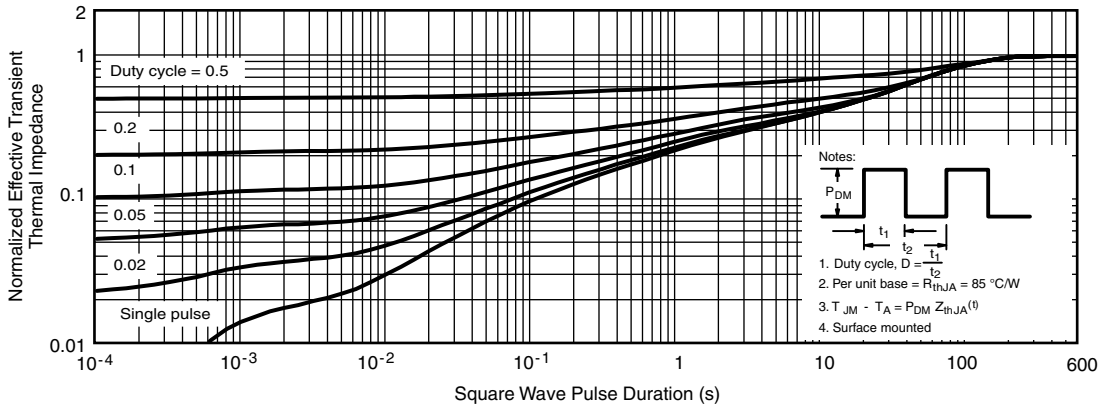


⁽¹⁾ $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

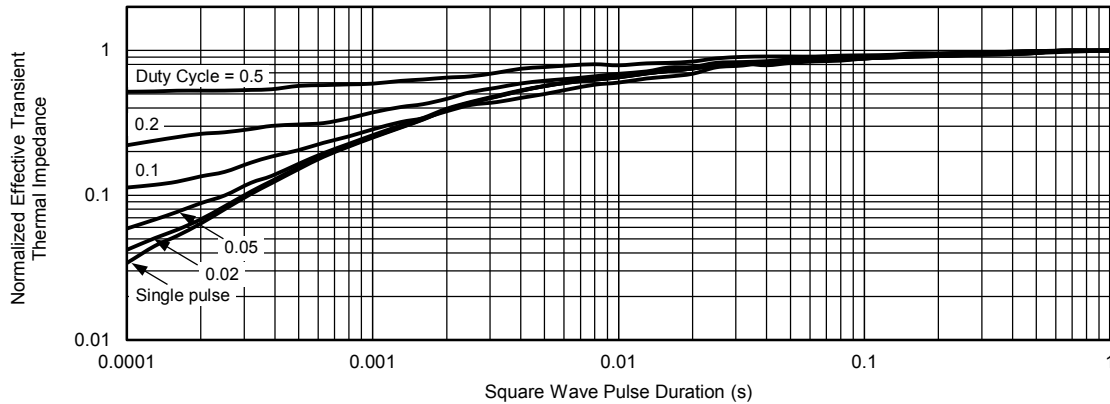
Safe Operating Area



N-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

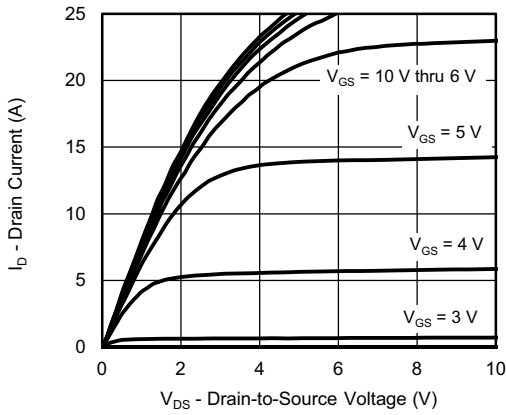


Normalized Thermal Transient Impedance, Junction-to-Case

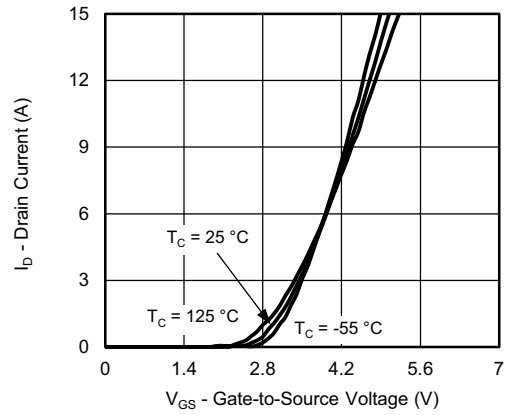
Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Case ($25\text{ }^\circ\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

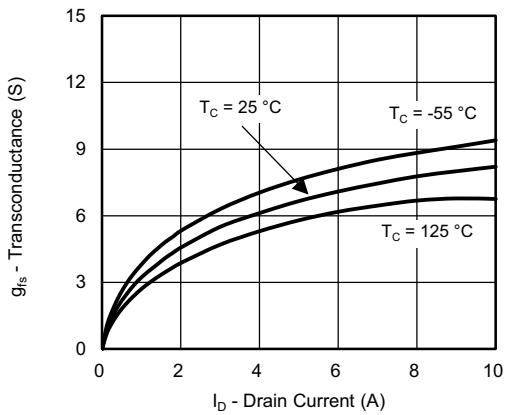
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



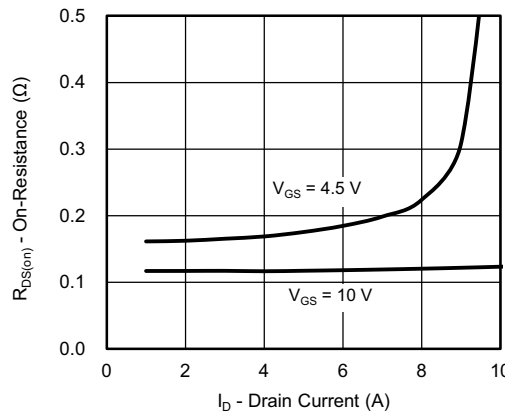
Output Characteristics



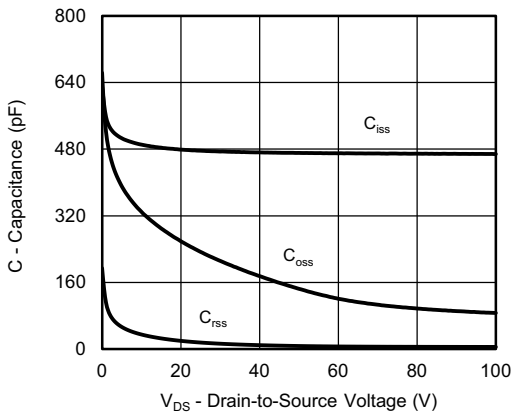
Transfer Characteristics



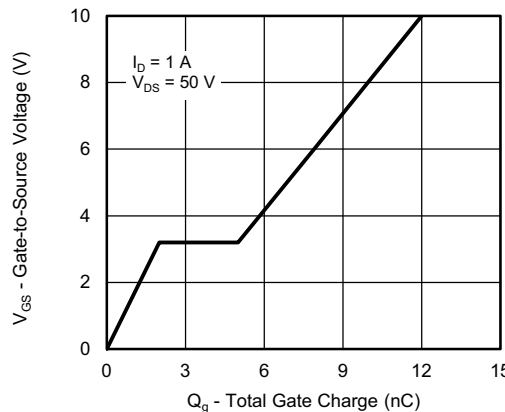
Transconductance



On-Resistance vs. Drain Current



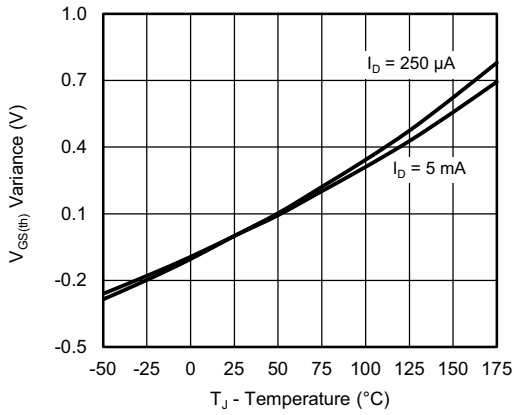
Capacitance



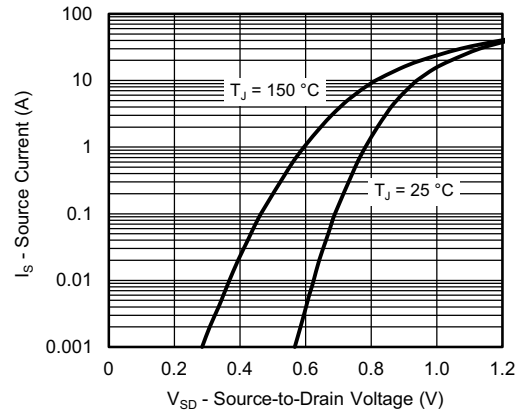
Gate Charge



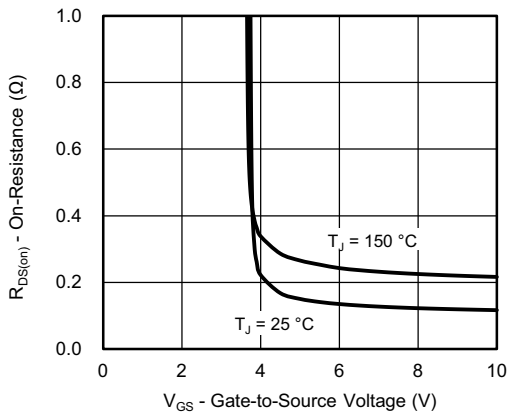
P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



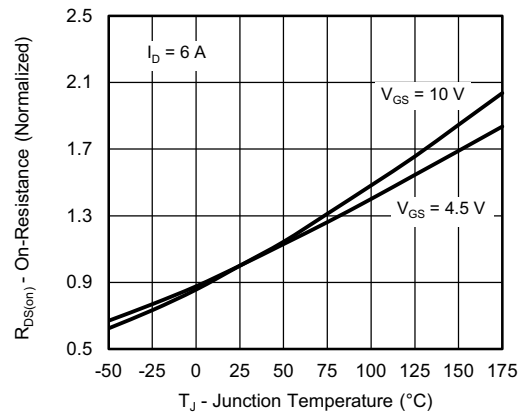
Threshold Voltage



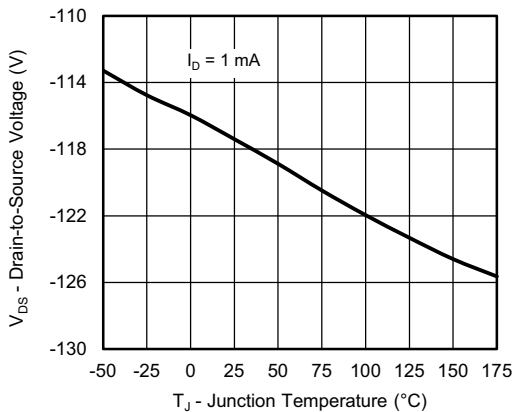
Source Drain Diode Forward Voltage



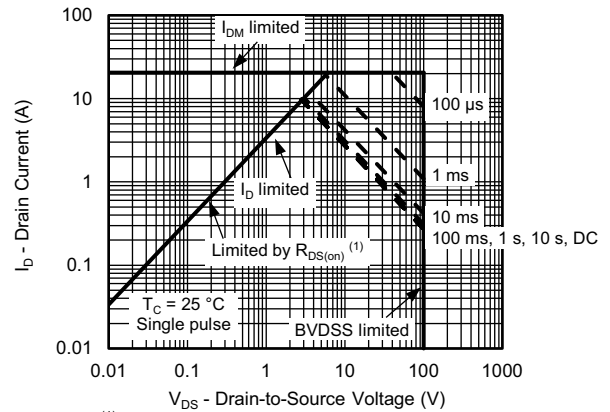
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Junction Temperature



Drain Source Breakdown vs. Junction Temperature

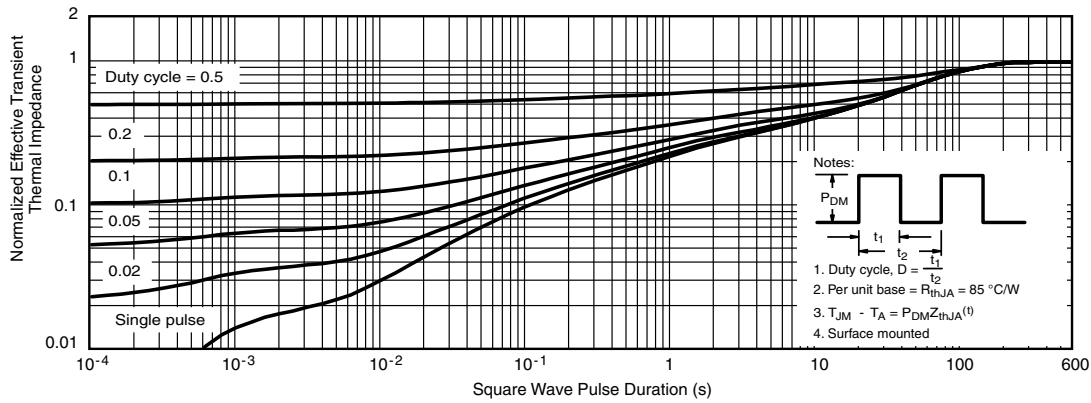


(1) $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

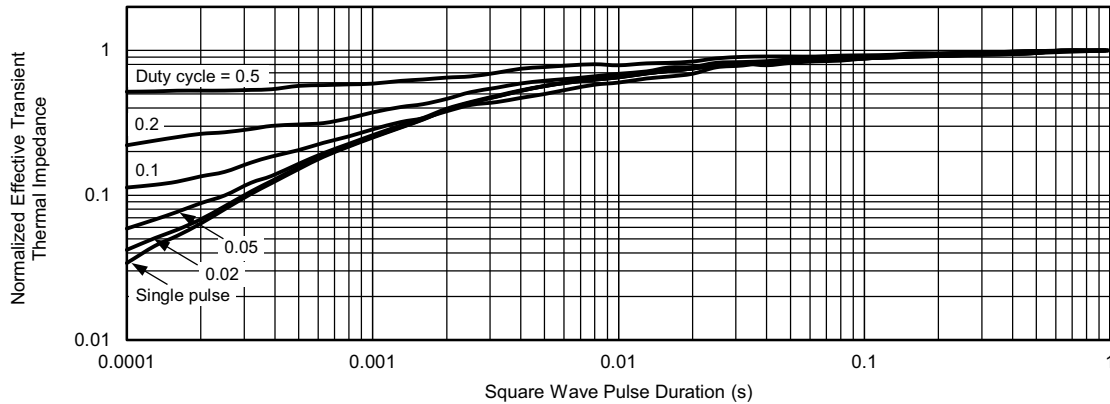
Safe Operating Area



P-CHANNEL TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^\circ\text{C}$)
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